

isc Silicon NPN Darlington Power Transistor

2SD1928

DESCRIPTION

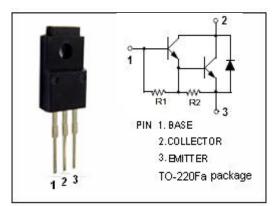
- · Collector-Emitter Saturation Voltage-
- : V_{CE(sat)}= 1.5V(Max) @I_C= 4A
- · High DC Current Gain
- : h_{FE}= 2000(Min) @ I_C= 4A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

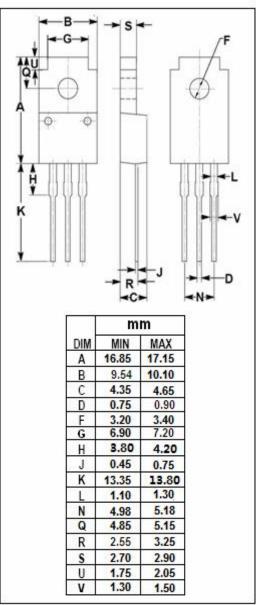
APPLICATIONS

 Designed for audio frequency power amplifier and low speed switching industrial use.

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL | PARAMETER VALUE | | UNIT | |
|------------------|--|---------|------------|--|
| V _{CBO} | Collector-Base Voltage | 100 | V | |
| V _{CEO} | Collector-Emitter Voltage | 100 | V | |
| V_{EBO} | Emitter-Base Voltage | 7 | V | |
| Ic | Collector Current-Continuous | 5 | Α | |
| ICP | Collector Current-Pulse | 12 | Α | |
| I _B | Base Current-Continuous | 0.8 | Α | |
| P _C | Collector Power Dissipation @ T _a =25°C | 2 | - W | |
| | Collector Power Dissipation @ T _c =25 °C | 20 | | |
| T _J | Junction Temperature | 150 | $^{\circ}$ | |
| T _{stg} | Storage Temperature Range | -55~150 | $^{\circ}$ | |







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ELECTRICAL CHARACTERISTICS

Tc=25℃ unless otherwise specified

| 16-25 C uniess otherwise specified | | | | | | | | | |
|------------------------------------|--------------------------------------|--|------|------|-------|------|--|--|--|
| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT | | | |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = 4A; I _B = 4mA | | | 1.5 | V | | | |
| V _{BE(sat)} | Base-Emitter Saturation Voltage | I _C = 4A; I _B = 4mA | | | 2.0 | V | | | |
| I _{CBO} | Collector Cutoff Current | V _{CB} = 100V; I _E = 0 | | | 10 | μА | | | |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 5V; I _C = 0 | | | 3.0 | mA | | | |
| h _{FE} -1 | DC Current Gain | Ic= 2A; V _{CE} = 2V | 2000 | | 20000 | | | | |
| h _{FE -2} | DC Current Gain | I _C = 6A; V _{CE} = 2V | 500 | | | | | | |
| Switching times | | | | | | | | | |
| ton | Turn-on Time | | | 0.4 | | μS | | | |
| t _{stg} | Storage Time | I _C = 4A, I _{B1} = I _{B2} = 4mA | | 2.5 | | μS | | | |
| t _f | Fall Time | | | 0.5 | | μS | | | |

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